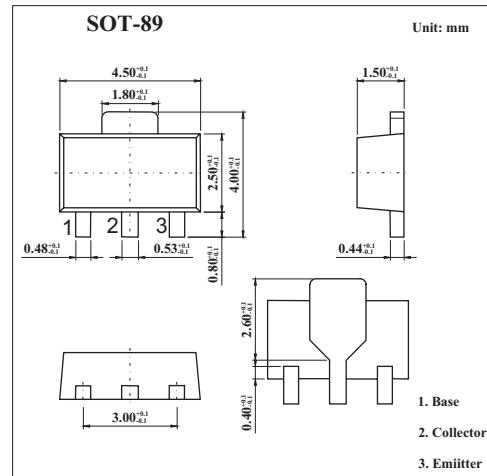


High Gain Amplifier Transistor

2SD2153



■ Features

- Low saturation voltage.
- Excellent DC current gain characteristics.

■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	30	V
Collector-emitter voltage	V _{CEO}	25	V
Emitter-base voltage	V _{EBO}	6	V
Collector current	I _C	2	A
Collector power dissipation	P _C	0.5	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV _{CBO}	I _C =50μA	30			V
Collector-emitter breakdown voltage	BV _{CEO}	I _C =1mA	25			V
Emitter-base breakdown voltage	BV _{EBO}	I _E =50μA	6			V
Collector cutoff current	I _{CBO}	V _{CB} =20V			0.5	μA
Emitter cutoff current	I _{EBO}	V _{EB} =5V			0.5	μA
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =1A, I _B =20mA		0.12	0.5	V
DC current transfer ratio	h _{FE}	V _{CE} =6V, I _C =0.5A	560		2700	
Output capacitance	f _T	V _{CE} =10V, I _E = -10mA, f=100MHz		110		MHz
Transition frequency	C _{ob}	V _{CB} =10V, I _E =0A, f=1MHz		22		pF

■ hFE Classification

Marking	DN		
Rank	U	V	W
hFE	560~1200	820~1800	1200~2700